

Technology	2021 Shuttle Code/Fab/Process Availability											
Process (Core/IO)	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
22nm (1P11M2T2A)	L222101 FAB12A			L222104 FAB12A		L222106 FAB12A			L222109 FAB12A			L222112 FAB12A
ULP/ULL (0.8V/1.8V, 0.8V/2.5V + ULVT/LVT/SVT/HVT/UHVT/EHVT) (SP SRAM / LL SRAM)	✓			✓		✓			✓			✓
28nm (1P11M2T2A)	L282101 FAB12A		X282103 USCXM		L282105 FAB12A		X282107 USCXM				L282111 FAB12A	X282112 USCXM
HLP (1.05V/1.8V, 1.05V/2.5V + LVT/RVT/HVT)(*1)	✓		✓		✓		✓				✓	✓
HPC+ (0.9V/1.8V, 0.9V/2.5V + uLVT/LVT/RVT/HVT/uHVT/eHVT)	✓		✓		✓		✓				✓	✓
HPC (0.9V/1.8V, 0.9V/2.5V + uLVT/LVT/RVT/HVT/uHVT)	✓		✓		✓		✓				✓	✓
EHV (1.0V/8V(+/-)10V)	✓		✓		✓		✓				✓	✓
LPT (1.05V/1.8V + LVT/RVT)	✓		✓		✓		✓				✓	✓
40nm (1P11M2T2H)		X402102 USCXM	S402103 FAB12i		L402105 FAB12A	X402106 USCXM		S402108 FAB12i	L402109 FAB12A	X402110 USCXM		S402112 FAB12i
40nm EFLASH(1.1V/0.9V LVT/RVT/HVT + 0.9V eLVT/eHVT + 2.5V (2.5V/OD3.3V/UD1.8V + 12V (12V/UD5V))			✓									✓
40nm HV :(core1.1V/(IO: 6V HV:32V),(IO: 8V HV:32V),(IO: 8V HV:20V))		✓	✓		✓	✓		✓	✓	✓		✓
40LP (1.1V / 1.8V(UD1.5V), 2.5V(UD1.8V/OD3.3V))		✓	✓		✓	✓		✓	✓	✓		✓
40ULL (1.1V/0.9V (uLVT/LVT/RVT/HVT) + 2.5V(OD_1.8V/OD_3.3V) + 0.9V(eLVT/eHVT))		✓	✓		✓	✓		✓	✓	✓		✓
55/65nm (1P10M2T2F)	S652101 FAB12i	X552102 USCXM	S652103 FAB12i	L552104 FAB12A	S652105 FAB12i		S652107 FAB12i	X552108 USCXM	L552109 FAB12A	S652110 FAB12i	X552111 USCXM	
65nm SP (1.0V/ 2.5V, 3.3V) (*2)	✓		✓		✓		✓			✓		
65nm LL (1.2V/ 1.8V, 2.5V(OD_3.3V) , 3.3V) (*3)	✓		✓		✓		✓			✓		
65nm LP (1.2V/ 2.5V(UD_1.8V/OD_3.3V)) (*4)	✓		✓		✓		✓			✓		
65nm LL URAM (1.2V/ 2.5V(OD_3.3V) , 3.3V)												
55nm SP (1.0V / 2.5V(OD_3.3V) , 3.3V)	✓		✓	✓	✓		✓		✓	✓		
55nm LP (1.2V / 2.5V(UD_1.8V / OD_3.3V))	✓		✓	✓	✓		✓		✓	✓		
55nm ULP(0.9~1.2V/2.5V(UD1.8V/OD3.3V))	✓			✓	✓				✓	✓		
55nm HV (1.2V / 6V(UD_5.5V , UD_3.3V) / 32V(+/-16V) + 16V(+/-8V))	✓		✓	✓	✓		✓		✓	✓		
55nm RFSOI (1.2V / 2.5V(UD_1.8))			✓				✓					
55nm EFLASH (1.2V (LVT/RVT/HVT/uHVT) + 2.5V(UD_1.8V/OD_3.3V) + HV_UD_5V)	✓	✓			✓			✓		✓	✓	
90nm (1P9M2T1F)									S902109 FAB12i			
90N (1.0V,1.2V / 1.8V , 2.5V(OD_3.3V) , 3.3V)									✓			

eFlash																			✓
0.5um/0.35um/0.3um/0.25um(*4) (2P3M)			P352103 FAB8AB								P352110 FAB8AB								
CDMOS / FDMOS (30V , 800V)			✓								✓								
0.3um/0.25um BCD (*5)			✓								✓								
0.35um MM			✓								✓								

Notes :

*1 : (12A) shall depend on reservation ratio to decide if provide, subject to change after kick-off.

*2 : (12i) LVT, MIM, 6X development in progress, pls contact account manager

*3 : (12i) 6X development in progress, pls contact account manager

*4 : (12i) MIM, 6X development in progress, pls contact account manager

*5 : 0.25um" is merely for "BCD" not for other standard STI process

* : The shuttle will be launched regularly if the minimum number of paidseats has been achieved. Otherwise, any adjustments to the schedule of planned shuttles will be subject to UMCs discretion.

M : Indicates maskallows formix-match among Fabs. Please note that in these cases, the wafer-Qutschedule of the 2nd Fab will be delayed by two weeks (domastic Fabsy four weeks (overseas Fåb) following the original schedule of the leading Fab.